Integrated Device Technology, Inc.

HIGH-SPEED 8K x 16 SEQUENTIAL ACCESS RANDOM ACCESS MEMORY (SARAM™)

IDT70825S/L

FEATURES:

- 8K x 16 Sequential Access Random Access Memory (SARAM™)
  - Sequential Access from one port and standard Random Access from the other port
  - Separate upper-byte and lower-byte control of the Random Access Port
- High-speed operation
  - 20ns t_{AA} for random access port
  - 20ns t_{CD} for sequential port
  - 25ns clock cycle time
- Architecture based on Dual-Port RAM cells
- Electrostatic discharge ≥ 2001V, Class II
- Compatible with Intel BMIC and 82430 PCI Set
- Width and Depth Expandable
- Sequential side
  - Address based flags for buffer control
  - Pointer logic supports two internal buffers
- Battery backup operation—2V data retention
- TTL-compatible, single 5V (±10%) power supply
- Available in 80-pin TQFP and 84-pin PGA
- Military product compliant to MIL-STD-883.
- Industrial temperature range (–40°C to +85°C) is available, tested to military electrical specifications.

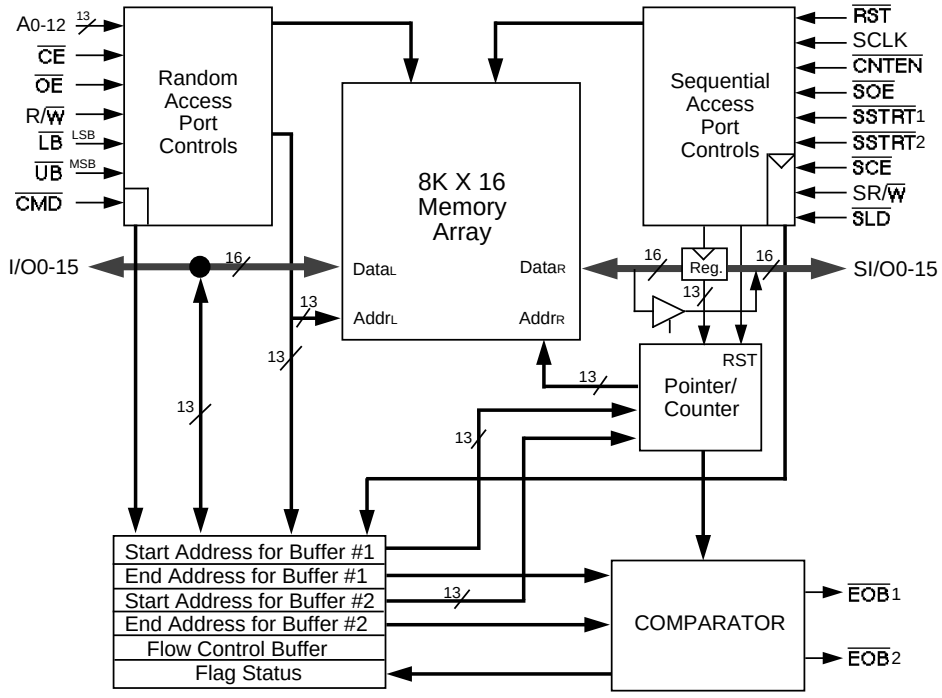
DESCRIPTION:

The IDT70825 is a high-speed 8K x 16-bit Sequential Access Random Access Memory (SARAM). The SARAM offers a single-chip solution to buffer data sequentially on one port, and be accessed randomly (asynchronously) through the other port. The device has a Dual-Port RAM based architecture with a standard SRAM interface for the random (asynchronous) access port, and a clocked interface with counter sequencing for the sequential (synchronous) access port.

Fabricated using CMOS high-performance technology, this memory device typically operates on less than 900mW of power at maximum high-speed clock-to-data and Random Access. An automatic power down feature, controlled by $\overline{CE}$, permits the on-chip circuitry of each port to enter a very low standby power mode.

The IDT70825 is packaged in a 80-pin Thin Plastic Quad Flatpack (TQFP) or 84-pin Ceramic Pin Grid Array (PGA). Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

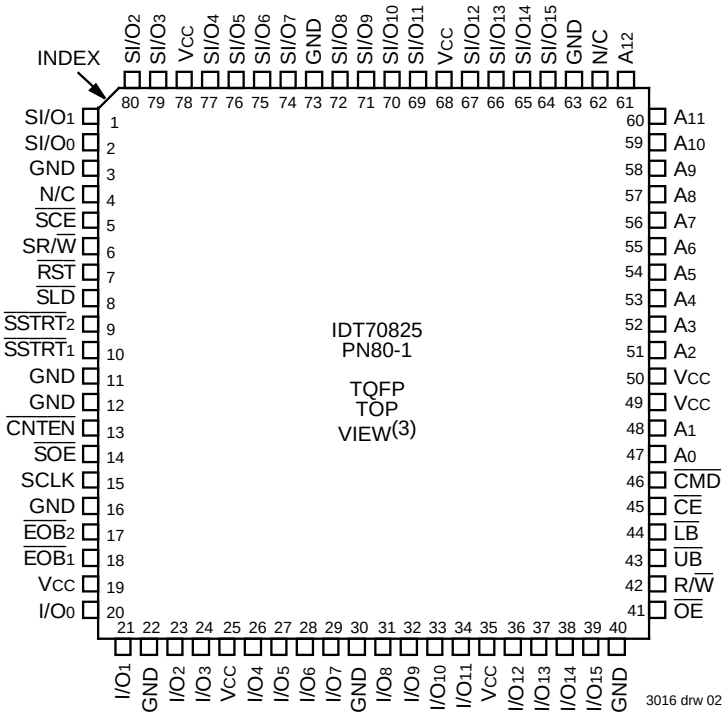
FUNCTIONAL BLOCK DIAGRAM

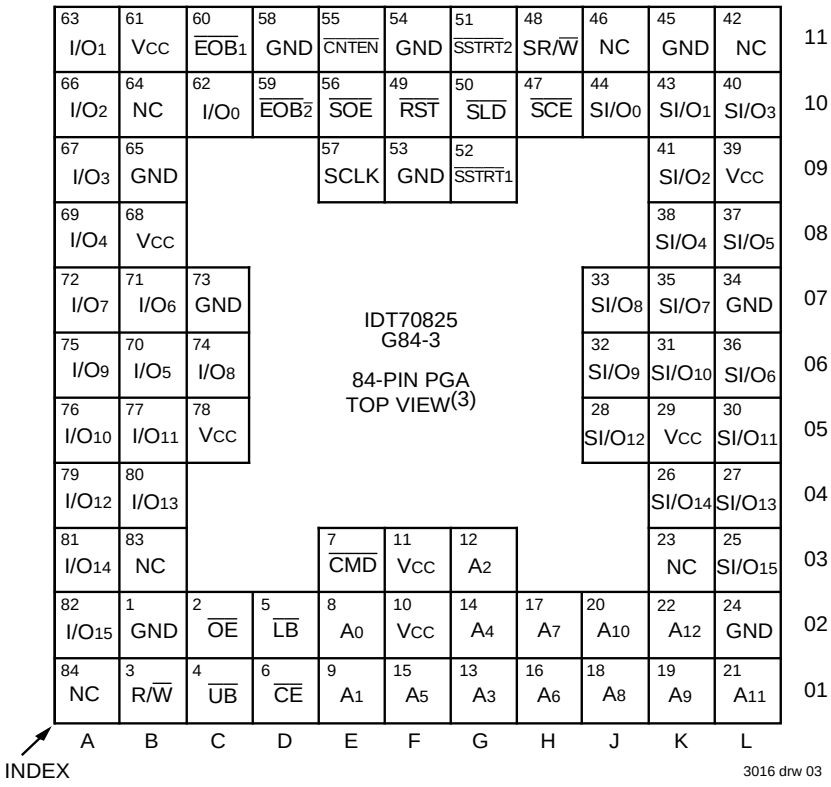


3016 drw 01

The IDT logo is a registered trademark and SARAM is a trademark of Integrated Device Technology, Inc.

PIN CONFIGURATIONS[1,2]





NOTES:
1. All VCC pins must be connected to power supply.
2. All GND pins must be connected to ground supply.
3. This text does not indicate orientation of the actual part-marking.

PIN DESCRIPTIONS: RANDOM ACCESS PORT

SYMBOL	NAME	I/O(1)	DESCRIPTION
A0-A12	Address Lines	I	Address inputs to access the 8192-word (16 bit) memory array.
I/O0-I/O15	Inputs/Outputs	I	Random access data inputs/outputs for 16-bit wide data.
$\overline{CE}$	Chip Enable	I	When $\overline{CE}$ is LOW, the random access port is enabled. When $\overline{CE}$ is HIGH, the random access port is disabled into power-down mode and the I/O outputs are in the high-impedance state. All data is retained during $\overline{CE}$ = VIH, unless it is altered by the sequential port. $\overline{CE}$ and $\overline{CMD}$ may not be LOW at the same time.
$\overline{CMD}$	Control Register Enable	I	When $\overline{CMD}$ is LOW, Address lines A0-A2, R/$\overline{W}$, and inputs/outputs I/O0-I/O11, are used to access the control register, the flag register, and the start and end of buffer registers. $\overline{CMD}$ and $\overline{CE}$ may not be LOW at the same time.
R/$\overline{W}$	Read/Write Enable	I	If $\overline{CE}$ is LOW and $\overline{CMD}$ is HIGH, data is written into the array when R/$\overline{W}$ is LOW and read out of the array when R/$\overline{W}$ is HIGH. If $\overline{CE}$ is HIGH and $\overline{CMD}$ is LOW, R/$\overline{W}$ is used to access the buffer command registers. $\overline{CE}$ and $\overline{CMD}$ may not be LOW at the same time.
$\overline{OE}$	Output Enable	I	When $\overline{OE}$ is LOW and R/$\overline{W}$ is HIGH, I/O0-I/O15 outputs are enabled. When $\overline{OE}$ is HIGH, the I/O outputs are in the high-impedance state.
$\overline{LB}$,$\overline{UB}$	Lower Byte, Upper Byte Enables	I	When $\overline{LB}$ is LOW, I/O0-I/O7 are accessible for read and write operations. When $\overline{LB}$ is HIGH, I/O0-I/O7 are tri-stated and blocked during read and write operations. $\overline{UB}$ controls access for I/O8-I/O15 in the same manner and is asynchronous from $\overline{LB}$.
VCC	Power Supply		Seven +5V power supply pins. All Vcc pins must be connected to the same +5V VCC supply.
GND	Ground		Ten Ground pins. All Ground pins must be connected to the same Ground supply.

3016 tbl 01

PIN DESCRIPTIONS: SEQUENTIAL ACCESS PORT

SYMBOL	NAME	I/O(1)	DESCRIPTION
SI/O0-15	Inputs	I/O	Sequential data inputs/outputs for 16-bit wide data.
SCLK	Clock	I	SI/O0-SI/O15, $\overline{SCE}$, SR/$\overline{W}$, and $\overline{SLD}$ are registered on the LOW-to-HIGH transition of SCLK. Also, the sequential access port address pointer increments by 1 on each LOW-to-HIGH transition of SCLK when $\overline{CNTEN}$ is LOW.
$\overline{SCE}$	Chip Enable	I	When $\overline{SCE}$ is LOW, the sequential access port is enabled on the LOW-to-HIGH transition of SCLK. When $\overline{SCE}$ is HIGH, the sequential access port is disabled into powered-down mode on the LOW-to-HIGH transition of SCLK, and the SI/O outputs are in the high-impedance state. All data is retained, unless altered by the random access port.
$\overline{CNTEN}$	Counter Enable	I	When $\overline{CNTEN}$ is LOW, the address pointer increments on the LOW-to-HIGH transition of SCLK. This function is independant of $\overline{SCE}$.
SR/$\overline{W}$	Read/Write Enable	I	When SR/$\overline{W}$ and $\overline{SCE}$ are LOW, a write cycle is initiated on the LOW-to-HIGH transition of SCLK. When SR/$\overline{W}$ is HIGH, and $\overline{SCE}$ and $\overline{SOE}$ are LOW, a read cycle is initiated on the LOW-to-HIGH transition of SCLK. Termination of a Write cycle is done on the Low-to-High transistion of SCLK if SR/$\overline{W}$ or $\overline{SCE}$ is High.
$\overline{SLD}$	Address Pointer Load Control	I	When $\overline{SLD}$ is sampled LOW, there is an internal delay of one cycle before the address pointer changes. When $\overline{SLD}$ is LOW, data on the inputs SI/O0-SI/O11 is loaded into a data-in register on the LOW-to-HIGH transition of SCLK. On the cycle following $\overline{SLD}$, the address pointer changes to the address location contained in the data-in register. $\overline{SSTRT}$1 and $\overline{SSTRT}$2 may not be LOW while $\overline{SLD}$ is LOW or during the cycle following $\overline{SLD}$.
$\overline{SSTRT}$1, $\overline{SSTRT}$2	Load Start of Address Register	I	When $\overline{SSTRT}$1 or $\overline{SSTRT}$2 is LOW, the start of address register #1 or #2 is loaded into the address pointer on the LOW-to-HIGH transition of SCLK. The start addresses are stored in internal registers. $\overline{SSTRT}$1 and $\overline{SSTRT}$2 may not be LOW while $\overline{SLD}$ is LOW or during the cycle following $\overline{SLD}$.
$\overline{EOB}$1, $\overline{EOB}$2	End of Buffer Flag	O	$\overline{EOB}$1 or $\overline{EOB}$2 is output LOW when the address pointer is incremented to match the address stored in the end of buffer registers. The flags can be cleared by either asserting $\overline{RST}$ LOW or by writing zero into bit 0 and/or bit 1 of the control register at address 101. $\overline{EOB}$1 and $\overline{EOB}$2 are dependent on separate internal registers, and therefore separate match addresses.
$\overline{SOE}$	Output Enable	I	$\overline{SOE}$ controls the data outputs and is independent of SCLK. When $\overline{SOE}$ is LOW, output buffers and the sequentially addressed data is output. When $\overline{SOE}$ is HIGH, the SI/O output bus is in the high-impedance state. $\overline{SOE}$ is asynchronous to SCLK.
$\overline{RST}$	Reset	I	When $\overline{RST}$ is LOW, all internal registers are set to their default state, the address pointer is set to zero and the $\overline{EOB}$1 and $\overline{EOB}$2 flags are set HIGH. $\overline{RST}$ is asynchronous to SCLK.

NOTE:

3016 tbl 02

1. "I/O" is bidirectional Input and Output. "I" is Input and "O" is Output.

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Rating	Commercial	Military	Unit
V_{TERM}(2)	Terminal Voltage with Respect to GND	–0.5 to +7.0	–0.5 to +7.0	V
T_A	Operating Temperature	0 to +70	–55 to +125	°C
T_{BIAS}	Temperature Under Bias	–55 to +125	–65 to +135	°C
T_{STG}	Storage Temperature	–55 to +125	–65 to +150	°C
I_{OUT}	DC Output Current	50	50	mA

NOTES: 3016 tbl 03

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. V_{TERM} must not exceed Vcc + 0.5V for more than 25% of the cycle time or 10ns maximum, and is limited to $\leq$ 20mA for the period of $V_{TERM} \geq$ Vcc + 0.5V.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Ambient Temperature	GND	VCC
Military	–55°C to +125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

3016 tbl 04

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{CC}	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V_{IH}	Input High Voltage	2.2	—	6.0(2)	V
V_{IL}	Input Low Voltage	–0.5(1)	—	0.8	V

NOTES: 3016 tbl 05

1. $V_{IL} \geq$ –1.5V for pulse width less than 10ns.
2. V_{TERM} must not exceed Vcc + 0.5V.

CAPACITANCE(1)

(T_A = +25°C, F = 1.0MHz)TQFP ONLY

Symbol	Parameter	Conditions(2)	Max.	Unit
C_{IN}	Input Capacitance	V_{IN} = 3dV	9	pF
C_{OUT}	Output Capacitance	V_{OUT} = 3dV	10	pF

NOTES: 3016 tbl 06

1. This parameter is determined by device characterization, but is not production tested.
2. 3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE (V_{CC} = 5.0V ± 10%)

Symbol	Parameter	Test Conditions	IDT70825S		IDT70825L		Unit
			Min.	Max.	Min.	Max.	
$\|I_{LI}\|$	Input Leakage Current(1)	V_{CC} = Max. V_{IN} = GND to V_{CC}	—	5.0	—	1.0	µA
$\|I_{LO}\|$	Output Leakage Current	V_{CC} = Max. $\overline{CE}$ and $\overline{SCE}$ = V_{IH} V_{OUT} = GND to V_{CC}	—	5.0	—	1.0	µA
V_{OL}	Output Low Voltage	I_{OL} = 4mA, V_{CC} = Min.	—	0.4	—	0.4	V
V_{OH}	Output High Voltage	I_{OH} = –4mA, V_{CC} = Min.	2.4	—	2.4	—	V

NOTE: 3016 tbl 07

1. At Vcc ≤ 2.0V input leakages are undefined.

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE(1) (V_{CC} = 5.0V ± 10%)

Symbol	Parameter	Test Condition	Version		70825X20 Com'l. Only Typ.(2)	70825X20 Com'l. Only Max.	70825X25 Com'l. Only Typ.(2)	70825X25 Com'l. Only Max.	70825X35 Typ.(2)	70825X35 Max.	70825X45 Typ.(2)	70825X45 Max.	Unit
I_{CC}	Dynamic Operating Current (Both Ports Active)	$\overline{CE}$ = V_{IL}, Outputs Open, $\overline{SCE}$ = V_{IL}(5) f = f_{MAX}(3)	MIL.	S	—	—	—	—	160	400	155	400	mA
				L	—	—	—	—	160	340	155	340	
			COM'L.	S	180	380	170	360	160	340	155	340	
				L	180	330	170	310	160	290	155	290	
I_{SB1}	Standby Current (Both Ports - TTL Level Inputs)	$\overline{SCE}$ and $\overline{CE}$ ≥ V_{IH}(7) $\overline{CMD}$ = V_{IH} f = f_{MAX}(3)	MIL.	S	—	—	—	—	20	85	16	85	mA
				L	—	—	—	—	20	65	16	65	
			COM'L.	S	25	70	25	70	20	70	16	70	
				L	25	50	25	50	20	50	16	50	
I_{SB2}	Standby Current (One Port - TTL Level Input)	$\overline{CE}$ or $\overline{SCE}$ = V_{IH} Active Port Outputs Open, f = f_{MAX}(3)	MIL.	S	—	—	—	—	95	290	90	290	mA
				L		——	—	—	95	250	90	250	
			COM'L.	S	115	260	105	250	95	240	90	240	
				L	115	230	105	220	95	210	90	210	
I_{SB3}	Full Standby Current (Both Ports - CMOS Level Inputs)	Both Ports $\overline{CE}$ and $\overline{SCE}$ ≥ V_{CC} - 0.2V(6,7) V_{IN} ≥ V_{CC} - 0.2V or V_{IN} ≤ 0.2V, f = 0(4)	MIL.	S	—	—	—	—	1.0	30	1.0	30	mA
				L	—	—	—	—	0.2	10	0.2	10	
			COM'L.	S	1.0	15	1.0	15	1.0	15	1.0	15	
				L	0.2	5	0.2	5	0.2	5	0.2	5	
I_{SB4}	Full Standby Current (One Port - CMOS Level Inputs)	One Port $\overline{CE}$ or $\overline{SCE}$ ≥ V_{CC} - 0.2V(6) Outputs Open (Active port), f = f_{MAX}(3) V_{IN} ≥ V_{CC} - 0.2V or V_{IN} ≤ 0.2V	MIL.	S	—	—	—	—	90	260	85	260	mA
				L	—	—	—	—	90	215	85	215	
			COM'L.	S	110	240	100	230	90	220	85	220	
				L	110	200	100	190	90	180	85	180	

NOTES: 3016 tbl 08

1. "X" in part number indicates power rating (S or L).
2. V_{CC} = 5V, Ta = +25°C; guaranteed by device characterization but not production tested.
3. At f = f_{MAX}, address, control lines (except Output Enable), and SCLK are cycling at the maximum frequency read cycle of 1/tRC.
4. f = 0 means no address or control lines change.
5. $\overline{SCE}$ may transition, but is Low ($\overline{SCE}$=V_{IL}) when clocked in by SCLK.
6. $\overline{SCE}$ may be ≤ 0.2V, after it is clocked in, since SCLK=V_{IH} must be clocked in prior to powerdown.
7. If one port is enabled (either $\overline{CE}$ or $\overline{SCE}$ = Low) then the other port is disabled ($\overline{SCE}$ or $\overline{CE}$ = High, respectively). CMOS High ≥ Vcc - 0.2V and Low ≤ 0.2V, and TTL High = V_{IH} and Low = V_{IL}.

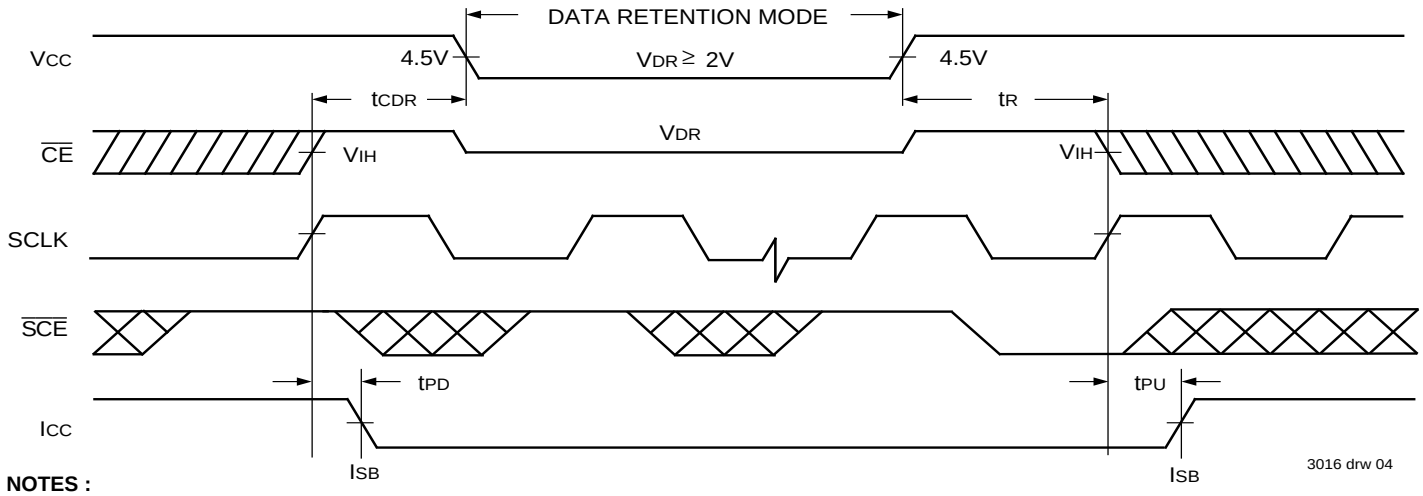
DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES (L VERSION ONLY) (V_{LC} ≤ 0.2V, V_{HC} ≥ V_{CC} - 0.2V)

Symbol	Parameter	Test Condition		Min.	Typ.(1)	Max.	Unit
V_{DR}	V_{CC} for Data Retention	V_{CC} = 2V		2.0	—	—	V
I_{CCDR}	Data Retention Current	$\overline{CE}$ = V_{HC}	MIL.	—	100	4000	µA
		V_{IN} = V_{HC} or = V_{LC}	COM'L.	—	100	1500	
t_{CDR}(3)	Chip Deselect to Data Retention Time	$\overline{SCE}$ = V_{HC}(4) when SCLK= ↗		0	—	—	ns
t_R(3)	Operation Recovery Time	$\overline{CMD}$ = V_{HC}		t_{RC}(2)	—	—	ns

NOTES : 3016 tbl 09

1. T_A = +25°C, V_{CC} = 2V; guaranteed by device characterization but not production tested.
2. t_{RC} = Read Cycle Time
3. This parameter is guaranteed by device characterization, but is not production tested.
4. To initiate data retention, $\overline{SCE}$ = V_{IH} must be clocked in.

DATA RETENTION AND POWER DOWN/UP WAVEFORM (RANDOM AND SEQUENTIAL PORT) (1,2)



NOTES :
1. $\overline{SCE}$ is synchronized to the sequential clock input.
2. $\overline{CMD} \geq V_{CC}$ - 0.2V.

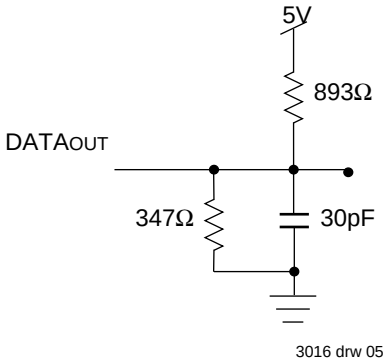


Figure 1. AC Output Test Load

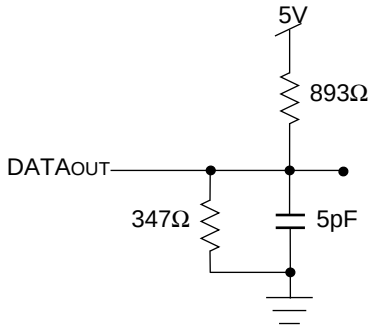


Figure 2. Output Test Load (for tCLZ, tBLZ, tOLZ, tCHZ, tBHZ, tOHZ, tWHZ, tCKHZ, and tCKLZ)
Including scope and jig.

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	Figures 1, 2, and 3

3016 tbl 10

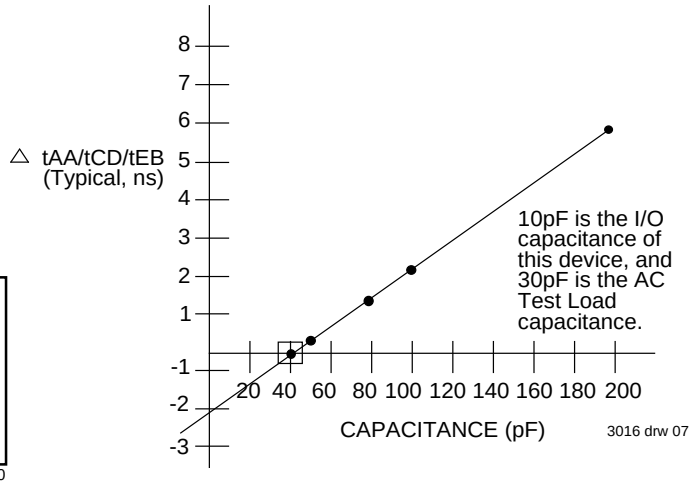


Figure 3. Lumped Capacitance Load Typical Derating Curve

TRUTH TABLE I – RANDOM ACCESS READ AND WRITE (1,2)

Inputs/Outputs								MODE
$\overline{CE}$	$\overline{CMD}$	R/$\overline{W}$	$\overline{OE}$	$\overline{LB}$	$\overline{UB}$	I/O$_0$-I/O$_7$	I/O$_8$-I/O-	
L	H	H	L	L	L	DATAOUT	DATAOUT	Read both Bytes.
L	H	H	L	L	H	DATAOUT	High-Z	Read lower Byte only.
L	H	H	L	H	L	High-Z	DATAOUT	Read upper Byte only.
L	H	L	H(3)	L	L	DATAIN	DATAIN	Write to both Bytes.
L	H	L	H(3)	L	H	DATAIN	High-Z	Write to lower Byte only.
L	H	L	H(3)	H	L	High-Z	DATAIN	Write to upper Byte only.
H	H	X	X	X	X	High-Z	High-Z	Both Bytes deselected and powered down.
L	H	H	H	X	X	High-Z	High-Z	Outputs disabled but not powered down.
L	H	X	X	H	H	High-Z	High-Z	Both Bytes deselected but not powered down.
H	L	L	H(3)	L(4)	L(4)	DATAIN	DATAIN	Write I/O$_0$-I/O$_{12}$ to the Buffer Command Register.
H	L	H	L	L(4)	L(4)	DATAOUT	DATAOUT	Read contents of the Buffer Command Register via I/O$_0$-I/O$_{12}$.

3016 tbl 11

NOTES:
1. H = V_{IH}, L = V_{IL}, X = Don't Care, and High-Z = High-impedance.
2. $\overline{RST}$, $\overline{SCE}$, $\overline{CNTEN}$, SR/$\overline{W}$, $\overline{SLD}$, $\overline{SSTRT1}$, $\overline{SSTRT2}$, SCLK, SI/O$_0$-SI/O$_{15}$, $\overline{EOB1}$, $\overline{EOB2}$, and $\overline{SOE}$ are unrelated to the random access port control and operation.
3. If $\overline{OE}$ = V_{IL} during write, t_{WHZ} must be added to the t_{WP} or t_{CW} write pulse width to allow the bus to float prior to being driven.
4. Byte operations to control register using $\overline{UB}$ and $\overline{LB}$ separately are also allowed.

TRUTH TABLE II – SEQUENTIAL READ (1,2,3,6,8)

Inputs/Outputs								MODE
SCLK	$\overline{SCE}$	$\overline{CNTEN}$	SR/$\overline{W}$	$\overline{EOB1}$	$\overline{EOB2}$	$\overline{SOE}$	SI/O	
↗	L	L	H	LOW	LAST	L	[EOB1]	Counter Advanced Sequential Read with $\overline{EOB}$1 reached.
↗	L	H	H	LAST	LAST	L	[EOB1 - 1]	Non-Counter Advanced Sequential Read, without $\overline{EOB}$1 reached.
↗	L	L	H	LAST	LOW	L	[EOB2]	Counter Advanced Sequential Read with $\overline{EOB}$2 reached.
↗	L	H	H	LAST	LAST	L	[EOB2 - 1]	Non-Counter Advanced Sequential Read without $\overline{EOB}$2 reached.
↗	L	L	H	LOW	LOW	H	HIGH-Z	Counter Advanced Sequential Non-Read with $\overline{EOB}$1 and $\overline{EOB}$2 reached.

3016 tbl 12

TRUTH TABLE III – SEQUENTIAL WRITE (1,2,3,4,5,6,7,8)

Inputs/Outputs								MODE
SCLK	$\overline{SCE}$	$\overline{CNTEN}$	SR/$\overline{W}$	$\overline{EOB1}$	$\overline{EOB2}$	$\overline{SOE}$	SI/O	
↗	L	H	L	LAST	LAST	H	SI/OIN	Non-Counter Advanced Sequential Write, without $\overline{EOB}$1 or $\overline{EOB}$2 reached
↗	L	L	L	LOW	LOW	H	SI/OIN	Counter Advanced Sequential Write with $\overline{EOB}$1 and $\overline{EOB}$2 reached.
↗	H	H	X	LAST	LAST	X	High-Z	No Write or Read due to Sequential port Deselect. No counter advance.
↗	H	L	X	NEXT	NEXT	X	High-Z	No Write or Read due to Sequential port Deselect. Conter does advance.

3016 tbl 13

NOTES:
1. H = V_{IH}, L = V_{IL}, X = Don't Care, and High-Z = High-impedance. LOW = V_{OL}.
2. $\overline{RST}$, $\overline{SLD}$, $\overline{SSTRT1}$, $\overline{SSTRT2}$ are continuously HIGH during a sequential write access, other than pointer access operations.
3. $\overline{CE}$, $\overline{OE}$, R/$\overline{W}$, $\overline{CMD}$, $\overline{LB}$, $\overline{UB}$, and I/O$_0$-I/O$_{15}$ are unrelated to the sequential port control and operation except for $\overline{CMD}$ which must not be used concurrently with the sequential port operation (due to the counter and register control). $\overline{CMD}$ should be HIGH ($\overline{CMD}$ = V_{IH}) during sequential port access.
4. $\overline{SOE}$ must be HIGH ($\overline{SOE}$=V_{IH}) prior to write conditions only if the previous cycle is a read cycle, since the data being written must be an input at the rising edge of the clock during the cycle in which SR/$\overline{W}$ = V_{IL}.
5. SI/OIN refers to SI/O$_0$-SI/O$_{15}$ inputs.
6. "LAST" refers to the previous value still being output, no change.
7. Termination of a write is done on the Low-to-High transition of SCLK if SR/$\overline{W}$ or $\overline{SCE}$ is High.
8. When $\overline{CLKEN}$=Low, the address is incremented on the next rising edge before any operation takes place. See the diagrams called "Sequential Counter Enable Cycle after Reset, Read (and write) Cycle".

TRUTH TABLE IV – SEQUENTIAL ADDRESS POINTER OPERATIONS (1,2,3,4,5)

Inputs/Outputs					MODE
SCLK	$\overline{SLD}$	$\overline{SSTRT1}$	$\overline{SSTRT2}$	$\overline{SOE}$	
↑	H	L	H	X	Start address for Buffer #1 loaded into Address Pointer.
↑	H	H	L	X	Start address for Buffer #2 loaded into Address Pointer.
↑	L	H	H	H(6)	Data on SI/O0-SI/O12 loaded into Address Pointer.

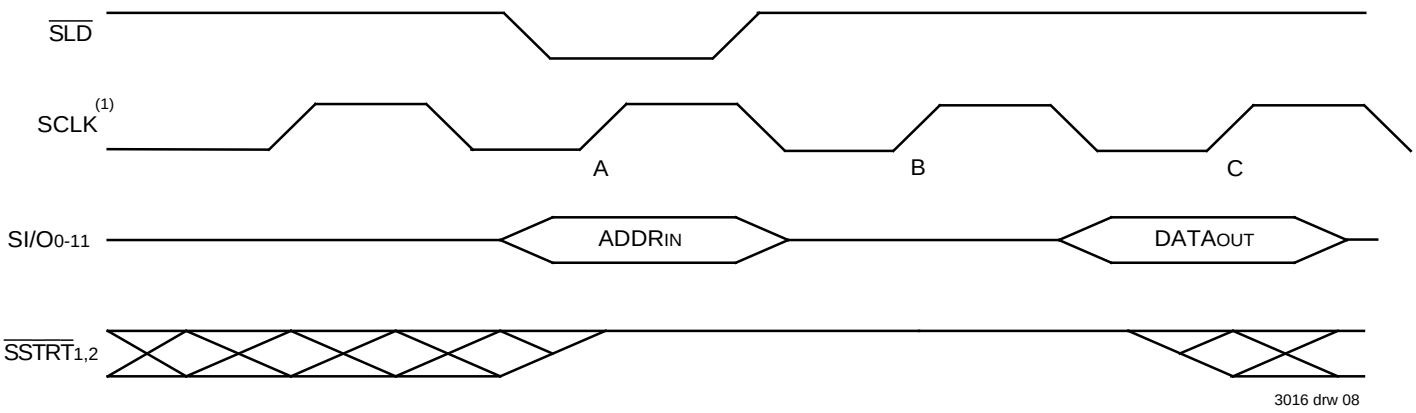
3016 tbl 14

NOTES:
1. H = V_{IH}, L = V_{IL}, X = Don't Care, and High-Z = High-impedance.
2. $\overline{RST}$ is continuously HIGH. The conditions of $\overline{SCE}$, $\overline{CNTEN}$, and SR/$\overline{W}$ are unrelated to the sequential address pointer operations.
3. $\overline{CE}$, $\overline{OE}$, R/$\overline{W}$, $\overline{LB}$, $\overline{UB}$, and I/O0-I/O15 are unrelated to the sequential port control and operation, except for $\overline{CMD}$ which must not be used concurrently with the sequential port operation (due to the counter and register control). $\overline{CMD}$ should be HIGH (CMD = V_{IH}) during sequential port access.
4. Address pointer can also change when it reaches an end of buffer address. See Flow Control Bits table.
5. When $\overline{SLD}$ is sampled LOW, there is an internal delay of one cycle before the address pointer changes. The state of $\overline{CNTEN}$ is ignored and the address is not incremented during the two cycles.
6. $\overline{SOE}$ may be LOW with $\overline{SCE}$ deselect or in the write mode using SR/$\overline{W}$.

ADDRESS POINTER LOAD CONTROL (SLD)

In $\overline{SLD}$ mode, there is an internal delay of one cycle before the address pointer changes in the cycle following $\overline{SLD}$. When $\overline{SLD}$ is LOW, data on the inputs SI/O0-SI/O12 is loaded into a data-in register on the LOW-to-HIGH transition of $\overline{SCLK}$. On the cycle following $\overline{SLD}$, the address pointer changes to the address location contained in the data-in register. $\overline{SSTRT1}$, $\overline{SSTRT2}$ may not be low while $\overline{SLD}$ is LOW, or during the cycle following $\overline{SLD}$. The $\overline{SSTRT1}$ and $\overline{SSTRT2}$ require only one clock cycle, since these addresses are pre-loaded in the registers already.

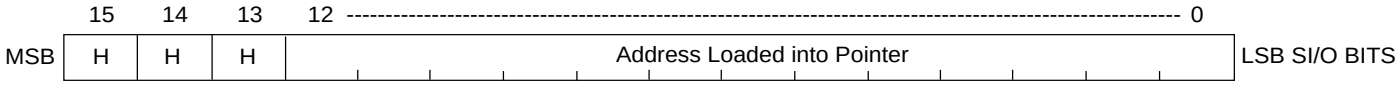
$\overline{SLD}$ MODE (1)



3016 drw 08

NOTE:
1. At SCLK edge (A), SI/O0-SI/O12 data is loaded into a data-in register. At edge (B), contents of the data-in register are loaded into the address pointer (i.e. address pointer changes). At SCLK edge (A), $\overline{SSTRT1}$ and $\overline{SSTRT2}$ must be high to ensure for proper sequential address pointer loading. At SCLK edge (B), $\overline{SLD}$ and $\overline{SSTRT1,2}$ must be high to ensure for proper sequential address pointer loading. For $\overline{SSTRT1}$ or $\overline{SSTRT2}$, the data to be read will be ready for edge (B), while data will not be ready at edge (B) when $\overline{SLD}$ is used, but will be ready at edge (C).

SEQUENTIAL LOAD OF ADDRESS INTO POINTER/COUNTER (1)



3016 drw 09

NOTE:
1. "H" = V_{IH} for the SI/O intput state.

Reset ($\overline{RST}$)

Setting $\overline{RST}$ LOW resets the control state of the SARAM. $\overline{RST}$ functions asynchronously of SCLK, (i.e. not registered). The default states after a reset operation are as follows:

Register	Contents
Address Pointer	0
EOB Flags	Cleared to High state
Buffer Flow Mode	BUFFER CHAINING
Start Address Buffer #1	0 (1)
End Address Buffer #1	4095 (4K)
Start Address Buffer #2	4096 (4K+1)
End Address Buffer #2	8191 (8K)
Registered State	$\overline{SCE}$ = VIH, SR/$\overline{W}$ = VIL

3016 tbl 15

BUFFER COMMAND MODE ($\overline{CMD}$)

Buffer Command Mode ($\overline{CMD}$) allows the random access port to control the state of the two buffers. Address pins A_0-A_2 and I/O pins I/O_0-I/O_{12} are used to access the start of buffer and the end of buffer addresses and to set the flow control mode of each buffer. The Buffer Command Mode also allows reading and clearing the status of the EOB flags. Seven different CMD cases are available depending on the conditions of A_0-A_2 and R/W. Address bits A_3-A_{12} and data I/O bits I/O_{13}-I/O_{15} are not used during this operation.

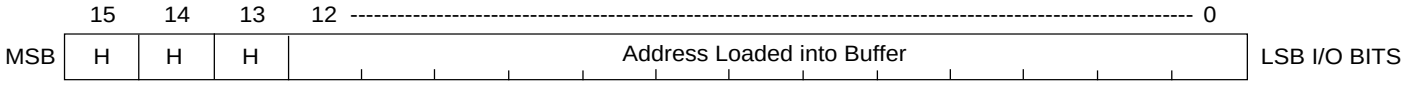
RANDOM ACCESS PORT $\overline{CMD}$ MODE(1)

Case #	A2-A0	R/$\overline{W}$	DESCRIPTIONS
1	000	0 (1)	Write (read) the start address of Buffer #1 through I/O_0-I/O_{12}.
2	001	0 (1)	Write (read) the end address of Buffer #1 through I/O_0-I/O_{12}.
3	010	0 (1)	Write (read) the start address of Buffer #2 through I/O_0-I/O_{12}.
4	011	0 (1)	Write (read) the end address of Buffer #2 through I/O_0-I/O_{12}.
5	100	0 (1)	Write (read) flow control register
6	101	0	Write only – clear EOB_1 and/or EOB_2 flag
7	101	1	Read only – flag status register
8	110/111	(X)	(Reserved)

3016 tbl 16

NOTE:
1. R/$\overline{W}$ input "0(1)" indicates a write(0) or read(1) occurring with the same address input.

CASES 1 THROUGH 4: START AND END OF BUFFER REGISTER DESCRIPTION(1,2)



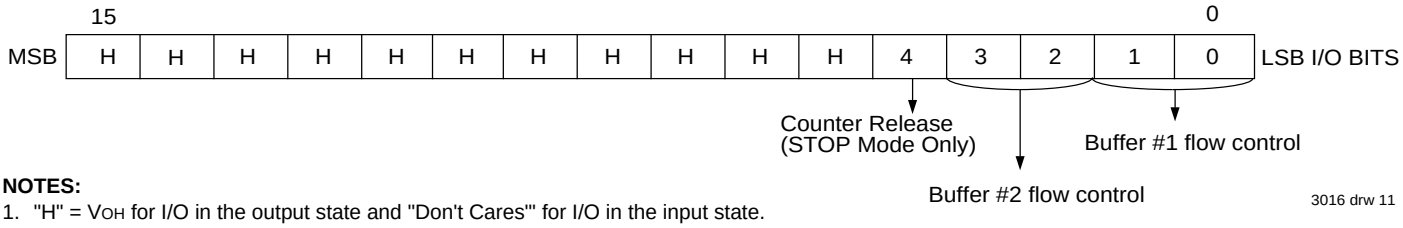
3016 drw 10

NOTES:
1. "H" = VOH for I/O in the output state and "Don't Cares" for I/O in the input state.
2. A write into the buffer occurs when R/$\overline{W}$ = VIL and a read when R/$\overline{W}$ = VIH. $\overline{EOB1}$/$\overline{SOB1}$ and $\overline{EOB2}$/$\overline{SOB2}$ are chosen through address A0-A2 while $\overline{CMD}$ = VIL and $\overline{CE}$ = VIH.

CASE 5: BUFFER FLOW MODES

Within the SARAM, the user can designate one of four buffer flow modes for each buffer. Each buffer flow mode defines a unique set of actions for the sequential port address pointer and EOB flags. In BUFFER CHAINING mode, after the address pointer reaches the end of the buffer, it sets the corresponding EOB flag and continues from the start address of the other buffer. In STOP mode, the address pointer stops incrementing after it reaches the end of the buffer. In LINEAR mode, the address pointer ignores the end of buffer address and increments past it, but sets the EOB flag. MASK mode is the same as LINEAR mode except EOB flags are not set.

FLOW CONTROL REGISTER DESCRIPTION(1,2)



3016 drw 11

NOTES:
1. "H" = VOH for I/O in the output state and "Don't Cares"' for I/O in the input state.
2. Writing a 0 into bit 4 releases the address pointer after it is stopped due to the STOP mode and allows sequential write operations to resume. This occurs asynchronously of SCLK, and therefore caution should be taken. The pointer will be at address EOB+2 on the next rising edge of SCLK that is enabled by $\overline{CNTEN}$. The pointer is also released by $\overline{RST}$, $\overline{SLD}$, $\overline{SSTRT1}$ and $\overline{SSTRT2}$ operations.

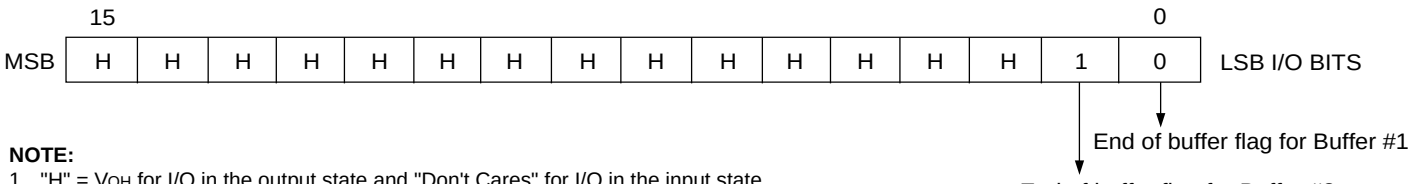
FLOW CONTROL BITS

Flow Control Bits		Functional Description
Bit 1 & Bit 0 (Bit 3 & Bit 2)	Mode	
00	BUFFER CHAINING	$\overline{EOB}$1 ($\overline{EOB}$2) is asserted (Active Low output) when the pointer matches the end address of Buffer #1 (Buffer #2). The pointer value is changed to the start address of Buffer #2 (Buffer #1).(1,3)
01	STOP	$\overline{EOB}$1 ($\overline{EOB}$2) is asserted when the pointer matches the end address of Buffer #1 (Buffer #2). The address pointer will stop incrementing when it reaches the next address ($\overline{EOB}$ address + 1), if $\overline{CNTEN}$ is Low on the next clock's rising edge. Otherwise, the address pointer will stop incrementing on $\overline{EOB}$. Sequential write operations are inhibited after the address pointer is stopped. The pointer can be released by bit 4 of the flow control register. (1,2,4)
10	LINEAR	$\overline{EOB}$1 ($\overline{EOB}$2) is asserted when the pointer matches the end address of Buffer #1 (Buffer #2). The pointer keeps incrementing for further operations.(1)
11	MASK	$\overline{EOB}$1 ($\overline{EOB}$2) is not asserted when the pointer reaches the end address of Buffer #1 (Buffer #2), although the flag status bits will be set. The pointer keeps incrementing for further operations.

3016 tbl 17

NOTES:
1. $\overline{EOB}$1 and $\overline{EOB}$2 may be asserted (set) at the same time, if both end addresses have been loaded with the same value.
2. $\overline{CMD}$ Flow Control bits are unchanged, the count does not continue advancement.
3. If $\overline{EOB}$1 and $\overline{EOB}$2 are equal, then the pointer will jump to the start of Buffer #1.
4. If counter has stopped at EOBx and was released by bit 4 of the flow control register, $\overline{CNTEN}$ must be LOW on the next rising edge of SCLK otherwise the flow control will remain in the STOP mode.

CASES 6 AND 7: FLAG STATUS REGISTER BIT DESCRIPTION(1)



3016 drw 12

NOTE:
1. "H" = VOH for I/O in the output state and "Don't Cares" for I/O in the input state.

CASE 6: FLAG STATUS REGISTER WRITE CONDITIONS(1)

Flag Status Bit 0, (Bit 1)	Functional Description
0	Clears Buffer Flag $\overline{EOB}$1, ($\overline{EOB}$2).
1	No change to the Buffer Flag.(2)

3016 tbl 18

NOTES:
1. Either bit 0 or bit 1, or both bits, may be changed simultaneously. One may be cleared while the second is left alone or cleared.
2. Remains as it was prior to the $\overline{CMD}$ operation, either HIGH (1) or LOW (0).

CASE 7: FLAG STATUS REGISTER READ CONDITIONS

Flag Status Bit 0, (Bit 1)	Functional Description
0	$\overline{EOB}$1 ($\overline{EOB}$2) flag has not been set, the Pointer has not reached the End of the Buffer.
1	$\overline{EOB}$1 ($\overline{EOB}$2) flag has been set, the Pointer has reached the End of the Buffer.

3016 tbl 19

CASES 8 AND 9: (RESERVED)

Illegal operations. All outputs will be HIGH on the I/O bus during a READ.

RANDOM ACCESS PORT: AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE (2,3)

Symbol	Parameter	IDT70825X20 Com'l. Only		IDT70825X25 Com'l. Only		IDT70825X35		IDT70825X45		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
tRC	Read Cycle Time	20	—	25	—	35	—	45	—	ns
tAA	Address Access Time	—	20	—	25	—	35	—	45	ns
tACE	Chip Enable Access Time	—	20	—	25	—	35	—	45	ns
tBE	Byte Enable Access Time	—	20	—	25	—	35	—	45	ns
tOE	Output Enable Access Time	—	10	—	10	—	15	—	20	ns
tOH	Output Hold from Address Change	3	—	3	—	3	—	3	—	ns
tCLZ	Chip Select Low-Z Time(1)	3	—	3	—	3	—	3	—	ns
tBLZ	Byte Enable Low-Z Time(1)	3	—	3	—	3	—	3	—	ns
tOLZ	Output Enable Low-Z Time(1)	2	—	2	—	2	—	2	—	ns
tCHZ	Chip Select High-Z Time(1)	—	10	—	12	—	15	—	15	ns
tBHZ	Byte Enable High-Z Time(1)	—	10	—	12	—	15	—	15	ns
tOHZ	Output Enable High-Z Time(1)	—	9	—	11	—	15	—	15	ns
tPU	Chip Select Power-Up Time	0	—	0	—	0	—	0	—	ns
tPD	Chip Select Power-Down Time	—	20	—	25	—	35	—	45	ns

NOTES: 3016 tbl 20

1. Transition measured at ±200mV from steady state. This parameter is guaranteed with the AC Test Load (Figure 2) by device characterization, but is not production tested.
2. "X" in part number indicates power rating (S or L).
3. $\overline{CMD}$ access follows standard timing listed for both read and write accesses, ($\overline{CE}$ = V_{IH} when $\overline{CMD}$ = V_{IL}) or ($\overline{CMD}$ = V_{IH} when $\overline{CE}$ = V_{IL}).

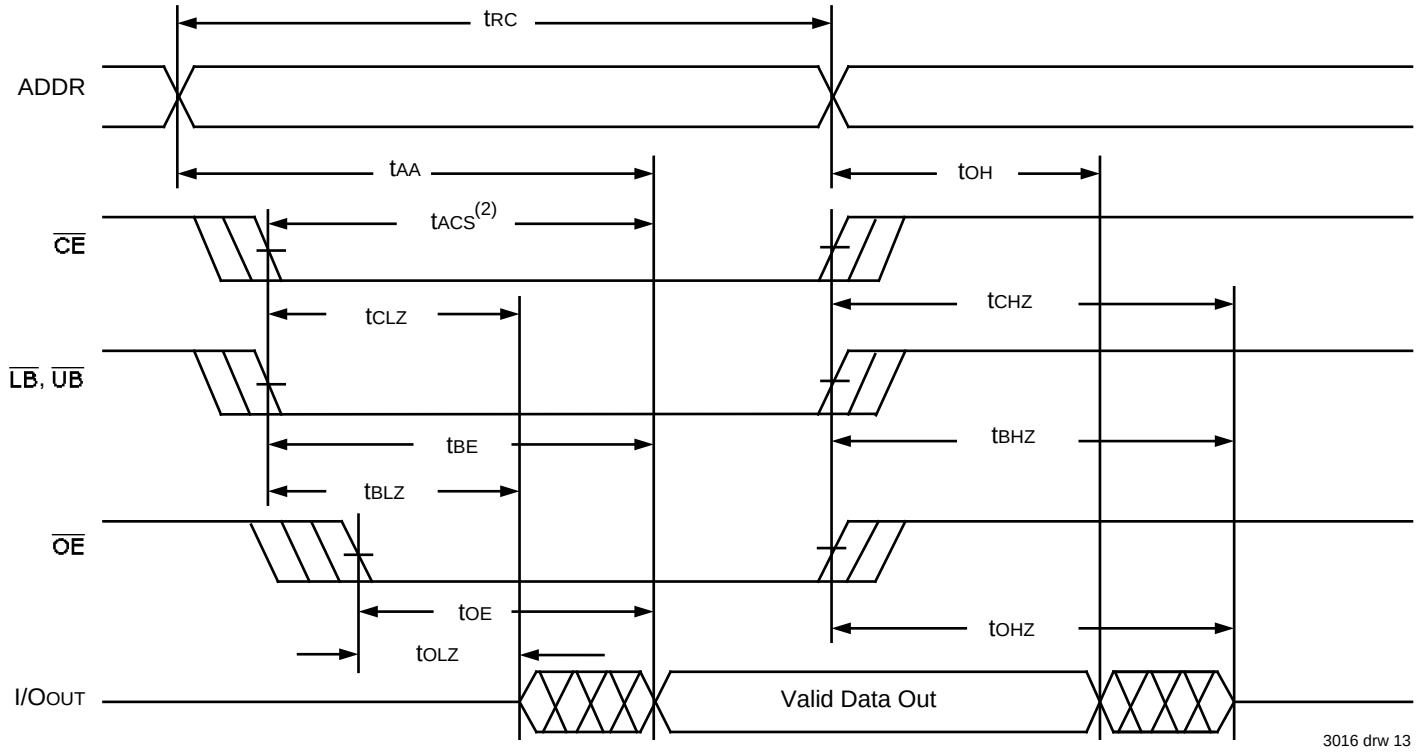
RANDOM ACCESS PORT: AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE (2,4)

Symbol	Parameter	IDT70825X20 Com'l. Only		IDT70825X25 Com'l. Only		IDT70825X35		IDT70825X45		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
WRITE CYCLE										
tWC	Write Cycle Time	20	—	25	—	35	—	45	—	ns
tCW	Chip Select to End-of-Write	15	—	20	—	25	—	30	—	ns
tAW	Address Valid to End-of-Write(3)	15	—	20	—	25	—	30	—	ns
tAS	Address Set-up Time	0	—	0	—	0	—	0	—	ns
tWP	Write Pulse Width(3)	13	—	20	—	25	—	30	—	ns
tBP	Byte Enable Pulse Width(3)	15	—	20	—	25	—	30	—	ns
tWR	Write Recovery Time	0	—	0	—	0	—	0	—	ns
tWHZ	Write Enable Output High-Z Time(1)	—	10	—	12	—	15	—	15	ns
tDW	Data Set-up Time	13	—	15	—	20	—	25	—	ns
tDH	Data Hold Time	0	—	0	—	0	—	0	—	ns
tOW	Output Active from End-of-Write	3	—	3	—	3	—	3	—	ns

NOTES: 3016 tbl 21

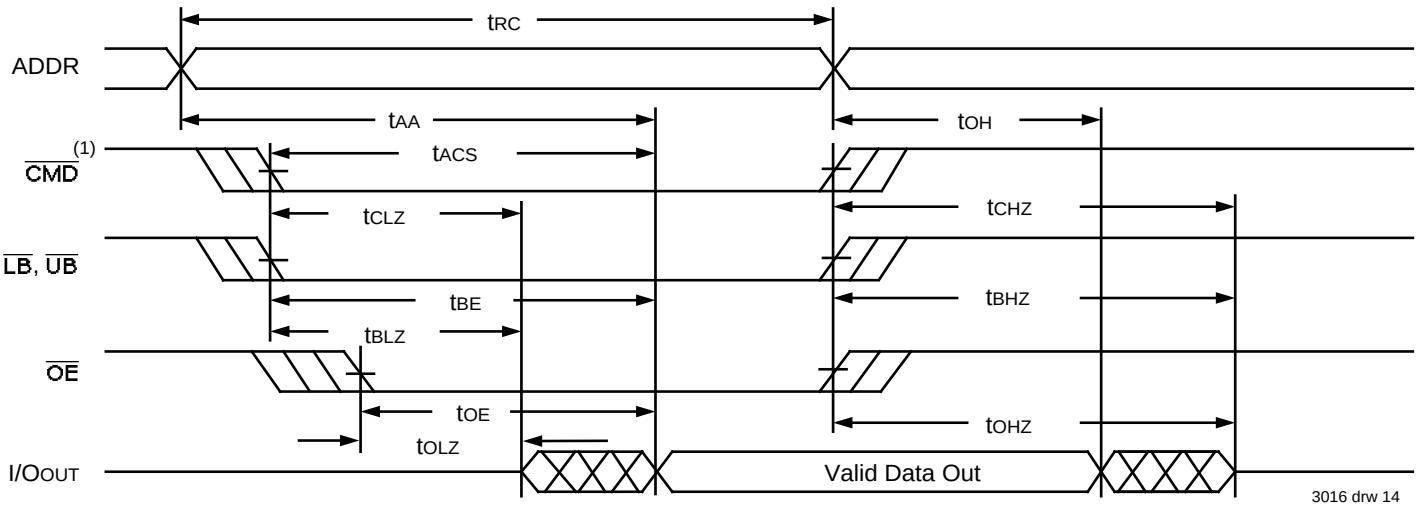
1. Transition measured at ±200mV from steady state. This parameter is guaranteed with the AC Test Load (Figure 2) by device characterization, but is not production tested.
2. "X" in part number indicates power rating (S or L).
3. $\overline{OE}$ is continuously HIGH, $\overline{OE}$ = V_{IH}. If during the R/$\overline{W}$ controlled write cycle the $\overline{OE}$ is LOW, t_{WP} must be greater or equal to t_{WHZ} + t_{DW} to allow the I/O drivers to turn off and on the data to be placed on the bus for the required t_{DW}. If $\overline{OE}$ is HIGH during the R/$\overline{W}$ controlled write cycle, this requirement does not apply and the minimum write pulse is the specified t_{WP}. For the $\overline{CE}$ controlled write cycle, $\overline{OE}$ may be LOW with no degradation to t_{CW} timing.
4. $\overline{CMD}$ access follows standard timing listed for both read and write accesses, ($\overline{CE}$ = V_{IH} when $\overline{CMD}$ = V_{IL}) or ($\overline{CMD}$ = V_{IH} when $\overline{CE}$ = V_{IL}).

RANDOM ACCESS PORT WAVEFORM: READ CYCLES (1,2)



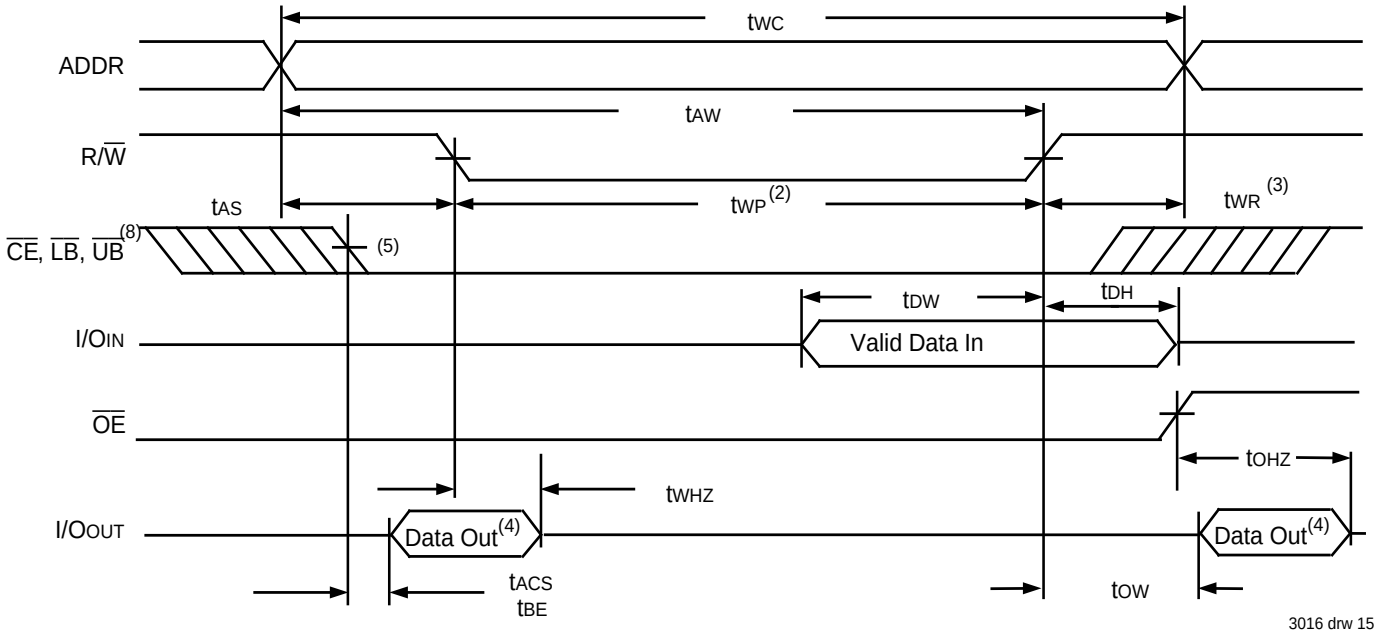
NOTES:
1. R/$\overline{W}$ is HIGH for Read cycle.
2. Address valid prior to or coincident with $\overline{CE}$ transition LOW; otherwise t_{AA} is the limiting parameter.

RANDOM ACCESS PORT WAVEFORM: READ CYCLES BUFFER COMMAND MODE



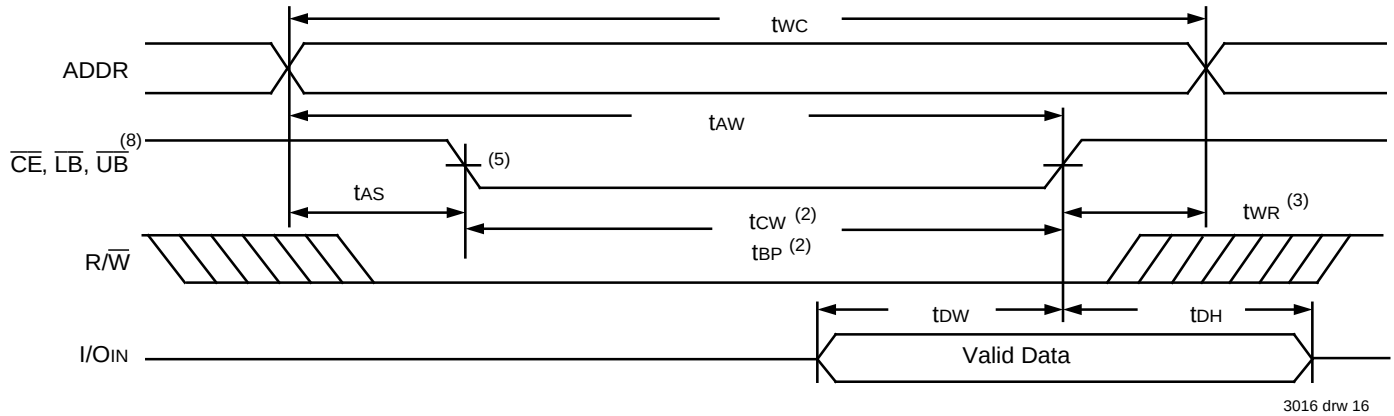
NOTE:
1. $\overline{CE}$ = V_{IH} when $\overline{CMD}$ = V_{IL}.

RANDOM ACCESS PORT WAVEFORM: WRITE CYCLE NO.1 (R/$\overline{W}$ CONTROLLED TIMING) (1,6)



3016 drw 15

RANDOM ACCESS PORT WAVEFORM: WRITE CYCLE NO.2 ($\overline{CE}$, $\overline{LB}$, AND/OR $\overline{UB}$ CONTROLLED TIMING) (1,6,7)



3016 drw 16

NOTES:
1. R/$\overline{W}$, $\overline{CE}$, or $\overline{LB}$ and $\overline{UB}$ must be inactive during all address transitions.
2. A write occurs during the overlap of R/$\overline{W}$ = V_{IL}, $\overline{CE}$ = V_{IL} and $\overline{LB}$ = V_{IL} and/or $\overline{UB}$ = V_{IL}.
3. t_{WR} is measured from the earlier of $\overline{CE}$ (and $\overline{LB}$ and/or $\overline{UB}$) or R/$\overline{W}$ going HIGH to the end of the write cycle.
4. During this period, I/O pins are in the output state and the input signals must not be applied.
5. If the $\overline{CE}$ LOW transition occurs simultaneously with or after the R/$\overline{W}$ LOW transition, the outputs remain in the High-impedance state.
6. $\overline{OE}$ is continuously HIGH, $\overline{OE}$ = V_{IH}. If during the R/$\overline{W}$ controlled write cycle the $\overline{OE}$ is LOW, t_{WP} must be greater or equal to t_{WHZ} + t_{DW} to allow the I/O drivers to turn off and on the data to be placed on the bus for the required t_{DW}. If $\overline{OE}$ is HIGH during the R/$\overline{W}$ controlled write cycle, this requirement does not apply and the minimum write pulse is the specified t_{WP}. For the $\overline{CE}$ controlled write cycle, $\overline{OE}$ may be LOW with no degregation to t_{CW} timing.
7. I/O_{OUT} is never enabled, therefore the output is in High-Z state during the entire write cycle.
8. $\overline{CMD}$ access follows the standard $\overline{CE}$ access described above. If $\overline{CMD}$ = V_{IL}, then $\overline{CE}$ must = V_{IH} or, when $\overline{CE}$ = V_{IL}, $\overline{CMD}$ must = V_{IH}.

SEQUENTIAL PORT: AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE(2)

Symbol	Parameter	IDT70825X20 Com'l. Only		IDT70825X25 Com'l. Only		IDT70825X35		IDT70825X45		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
tCYC	Sequential Clock Cycle Time	25	—	30	—	40	—	50	—	ns
tCH	Clock Pulse High	10	—	12	—	15	—	18	—	ns
tCL	Clock Pulse Low	10	—	12	—	15	—	18	—	ns
tES	Count Enable and Address Pointer Set-up Time	5	—	5	—	6	—	6	—	ns
tEH	Count Enable and Address Pointer Hold Time	2	—	2	—	2	—	2	—	ns
tSOE	Output Enable to Data Valid	—	8	—	10	—	15	—	20	ns
tOLZ	Output Enable Low-Z Time(1)	2	—	2	—	2	—	2	—	ns
tOHZ	Output Enable High-Z Time(1)	—	9	—	11	—	15	—	15	ns
tCD	Clock to Valid Data	—	20	—	25	—	35	—	45	ns
tCKHZ	Clock High-Z Time(1)	—	12	—	14	—	17	—	20	ns
tCKLZ	Clock Low-Z Time(1)	3	—	3	—	3	—	3	—	ns
tEB	Clock to EOB	—	13	—	15	—	18	—	23	ns

NOTES:
3016 tbl 22

1. Transition measured at ±200mV from steady state. This parameter is guaranteed with the AC Test Load (Figure 2) by device characterization, but is not production tested.
2. "X" in part numbers indicates power rating (S or L).

SEQUENTIAL PORT: AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE(1)

Symbol	Parameter	IDT70825X20 Com'l. Only		IDT70825X25 Com'l. Only		IDT70825X35		IDT70825X45		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
WRITE CYCLE										
tCYC	Sequential Clock Cycle Time	25	—	30	—	40	—	50	—	ns
tFS	Flow Restart Time	13	—	15	—	20	—	20	—	ns
tWS	Chip Select and Read/Write Set-up Time	5	—	5	—	6	—	6	—	ns
tWH	Chip Select and Read/Write Hold Time	2	—	2	—	2	—	2	—	ns
tDS	Input Data Set-up Time	5	—	5	—	6	—	6	—	ns
tDH	Input Data Hold Time	2	—	2	—	2	—	2	—	ns

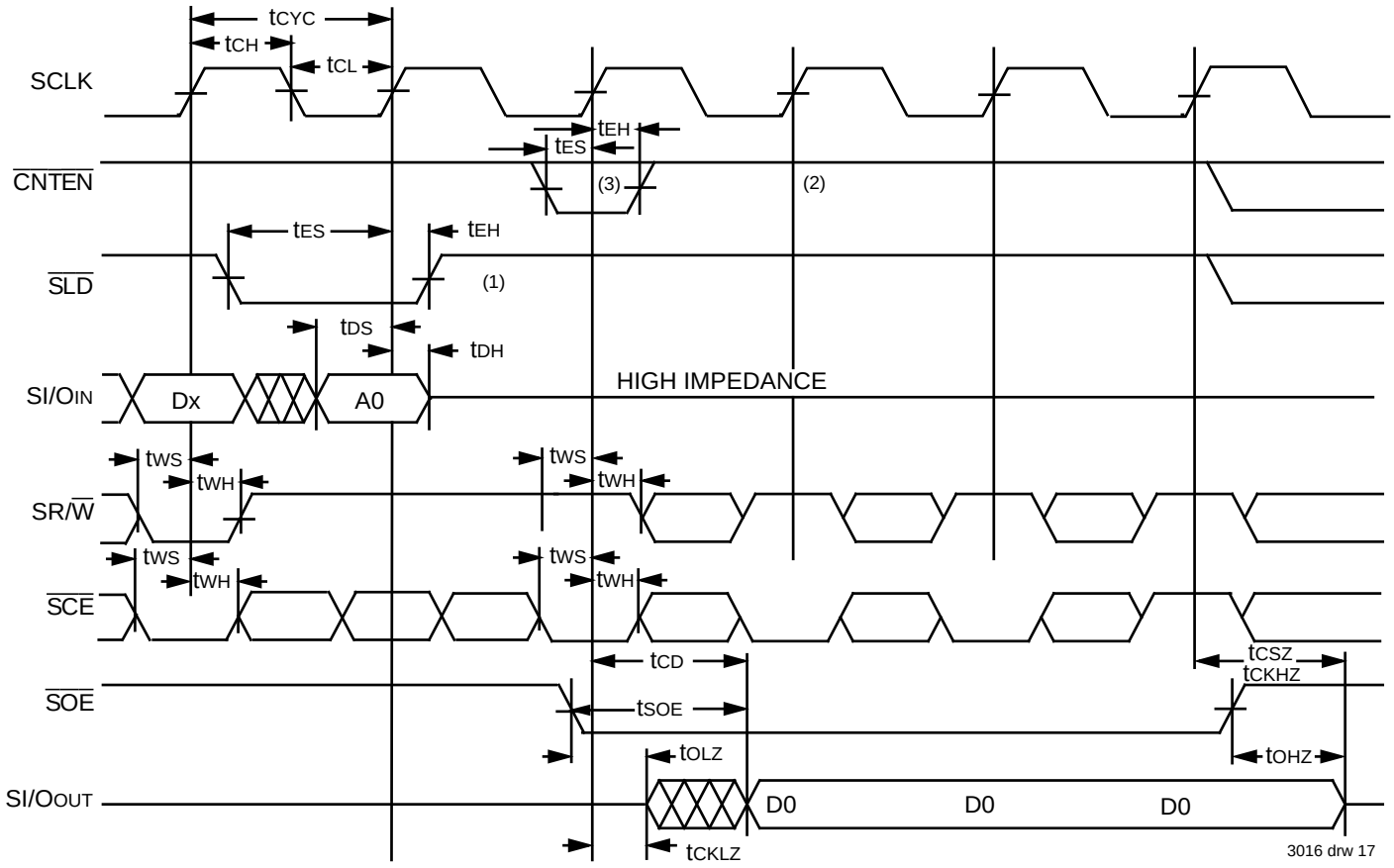
NOTE:
1. "X" in part numbers indicates power rating (S or L).
3016 tbl 23

SEQUENTIAL PORT: AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE(1)

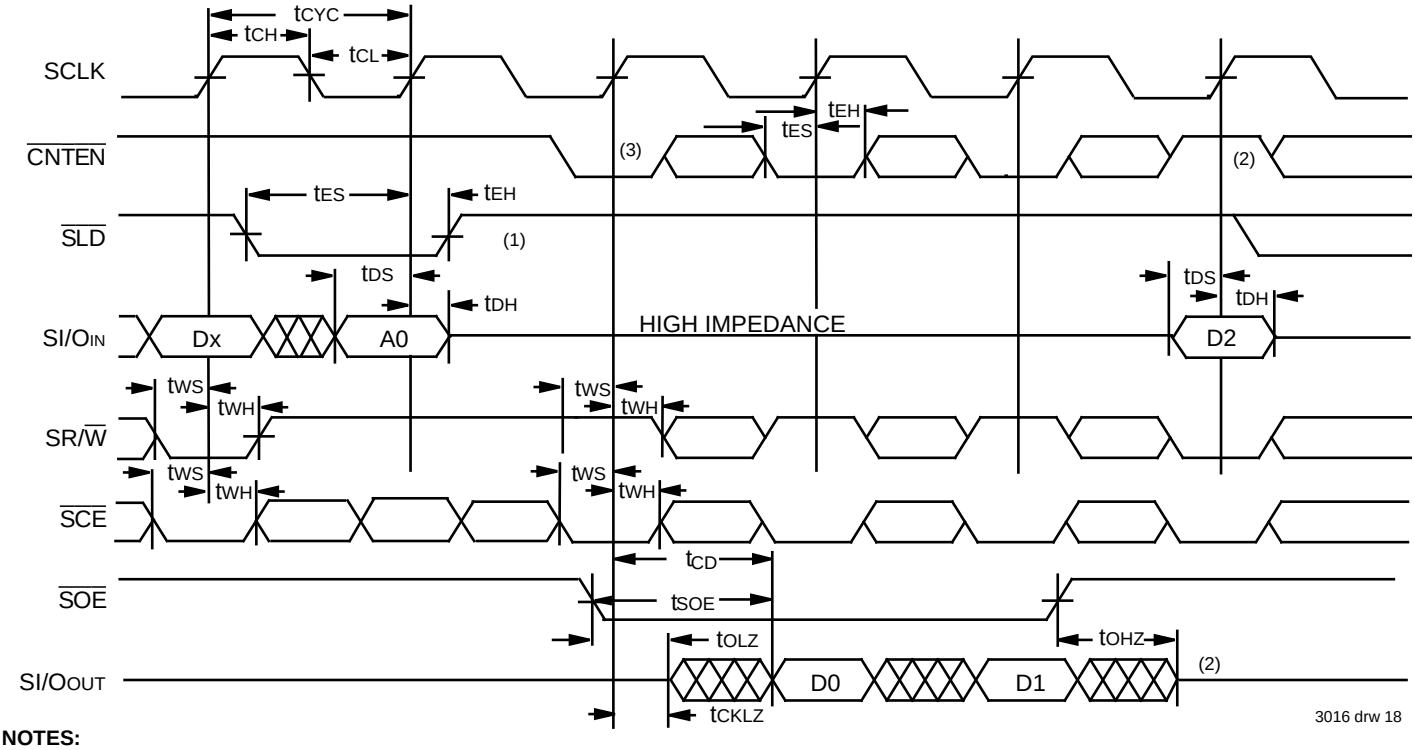
Symbol	Parameter	IDT70825X20 Com'l. Only		IDT70825X25 Com'l. Only		IDT70825X35		IDT70825X45		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
RESET CYCLE										
tRSPW	Reset Pulse Width	13	—	15	—	20	—	20	—	ns
tWERS	Write Enable High to Reset High	10	—	10	—	10	—	10	—	ns
tRSRC	Reset High to Write Enable Low	10	—	10	—	10	—	10	—	ns
tRSFV	Reset High to Flag Valid	15	—	20	—	25	—	25	—	ns

NOTE:
1. "X" in part numbers indicates power rating (S or L).
3016 tbl 24

SEQUENTIAL PORT WAVEFORM: WRITE, POINTER LOAD, NON-INCREMENTING READ

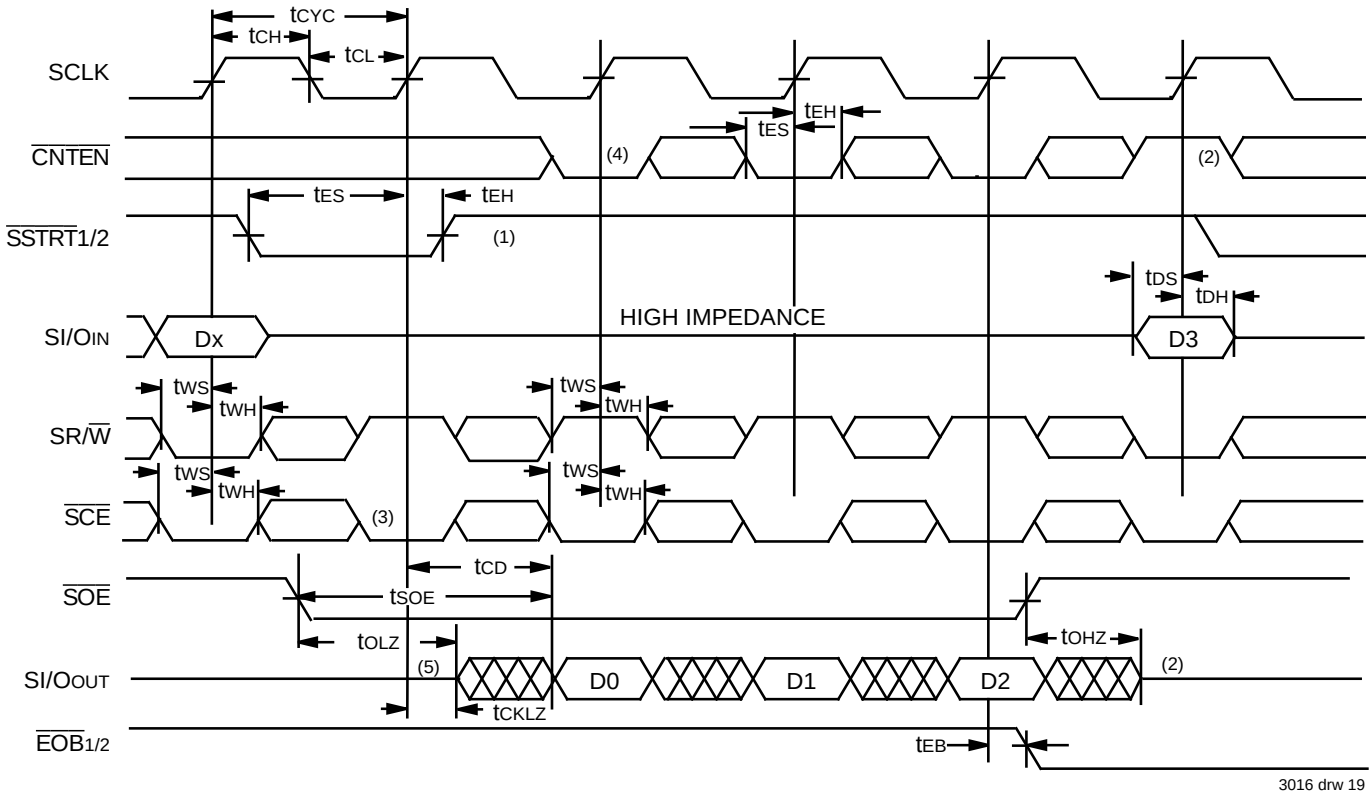


SEQUENTIAL PORT WAVEFORM: WRITE, POINTER LOAD, BURST READ



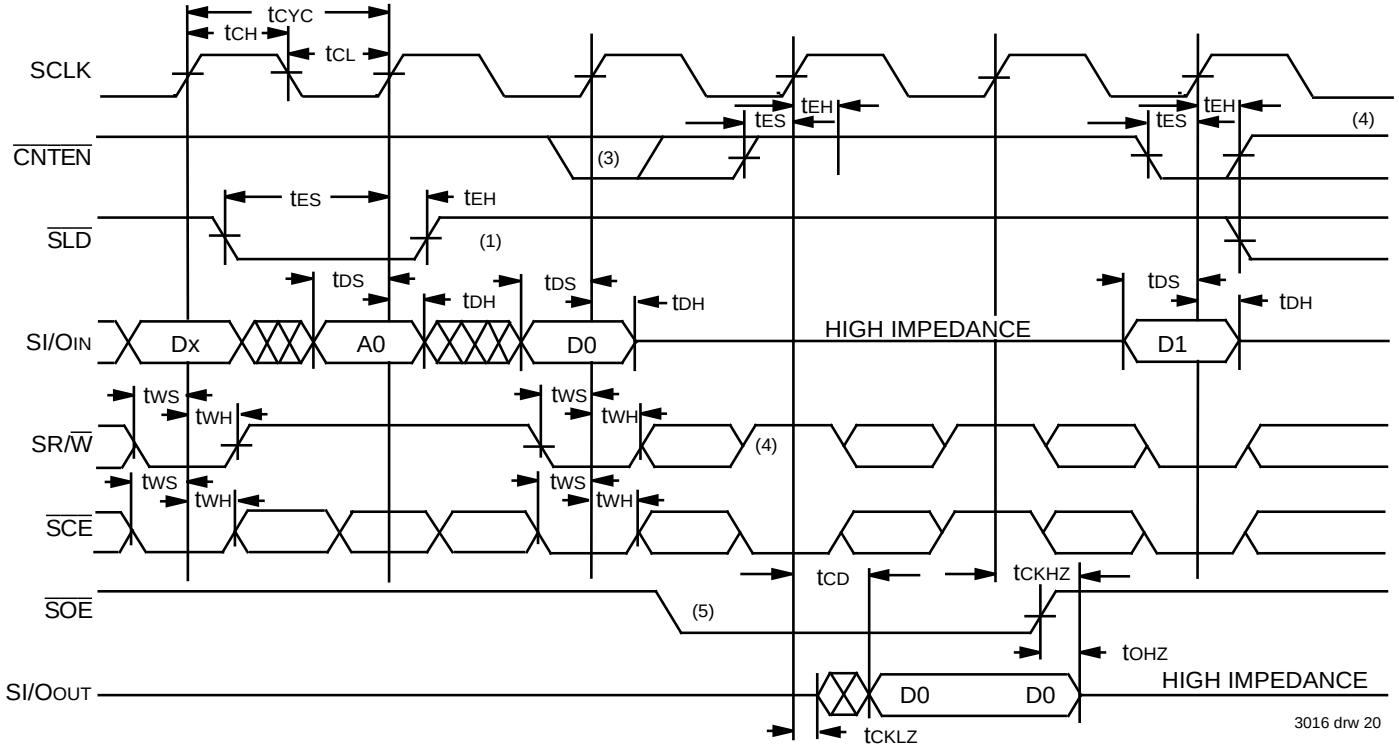
NOTES:
1. If $\overline{SLD}$ = V_{IL}, then address will be clocked in on the SCLK's rising edge.
2. If $\overline{CNTEN}$ = V_{IH} for the SCLK's rising edge, the internal address counter will not advance.
3. Pointer is not incremented on cycle immediately following $\overline{SLD}$ even if $\overline{CNTEN}$ is LOW.

SEQUENTIAL PORT WAVEFORM: READ STRT/EOB FLAG TIMING

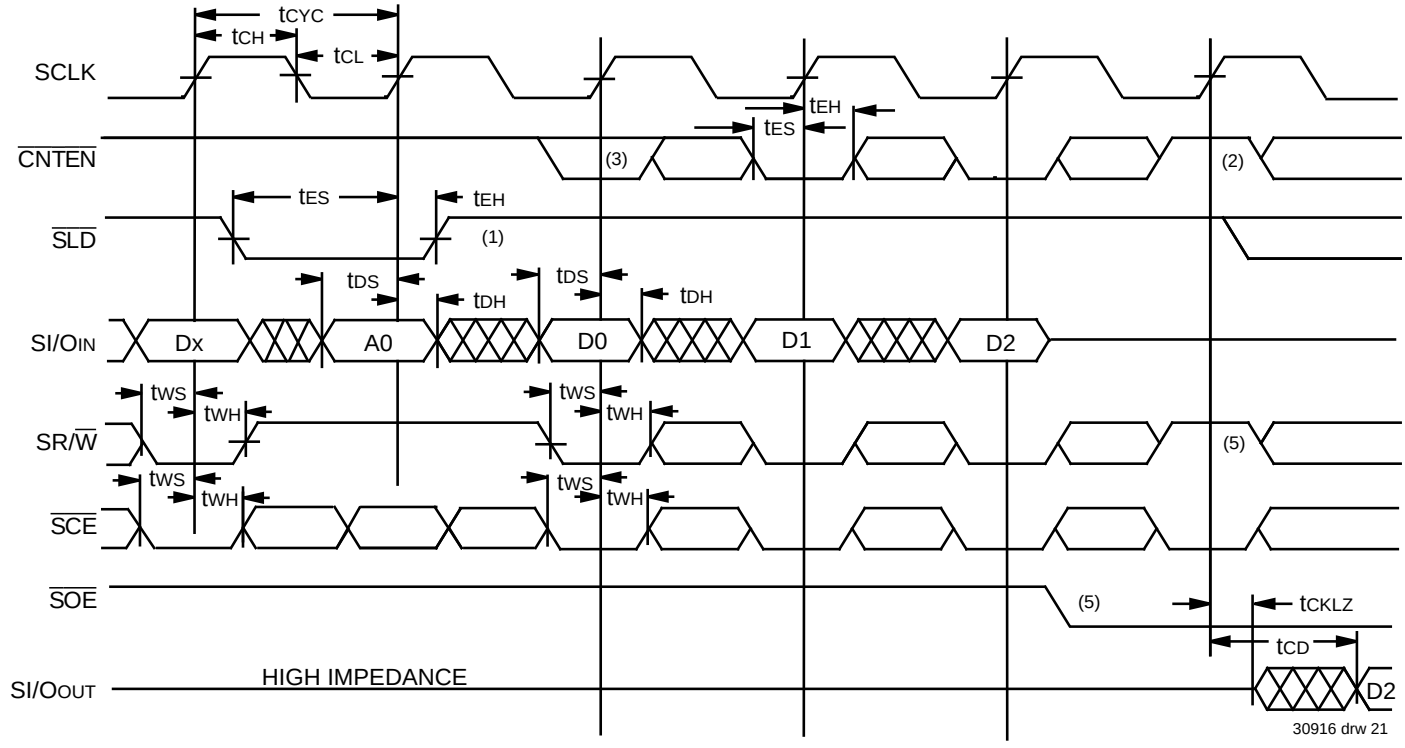


NOTES:
1. If $\overline{SSTRT_1}$ or $\overline{SSTRT_2}$ = V_{IL}, then address will be clocked in on the SCLK's rising edge.
2. If $\overline{CNTEN}$ = V_{IH} for the SCLK's rising edge, the internal address counter will not advance.
3. $\overline{SOE}$ will control the output and should be High on Power-Up. If $\overline{SCE}$ = V_{IL} and is clocked in while SR/$\overline{W}$ = V_{IH}, the data addressed will be read out within that cycle. If $\overline{SCE}$ = V_{IL} and is clocked in while SR/$\overline{W}$ = V_{IL}, the data addressed will be written to if the last cycle was a Read. $\overline{SOE}$ may be used to control the bus contention and permit a Write on this cycle.
4. Unlike $\overline{SLD}$ case, $\overline{CNTEN}$ is not disabled on cycle immediately following $\overline{SSTRT}$.
5. If SR/$\overline{W}$ = V_{IL}, data would be written to D0 again since $\overline{CNTEN}$ = V_{IH}.
6. $\overline{SOE}$ = V_{IL} makes no difference at this point since the SR/$\overline{W}$ = V_{IL} disables the output until SR/$\overline{W}$ = V_{IH} is clocked in on the next rising clock edge.

SEQUENTIAL PORT WAVEFORM: WRITE CYCLES

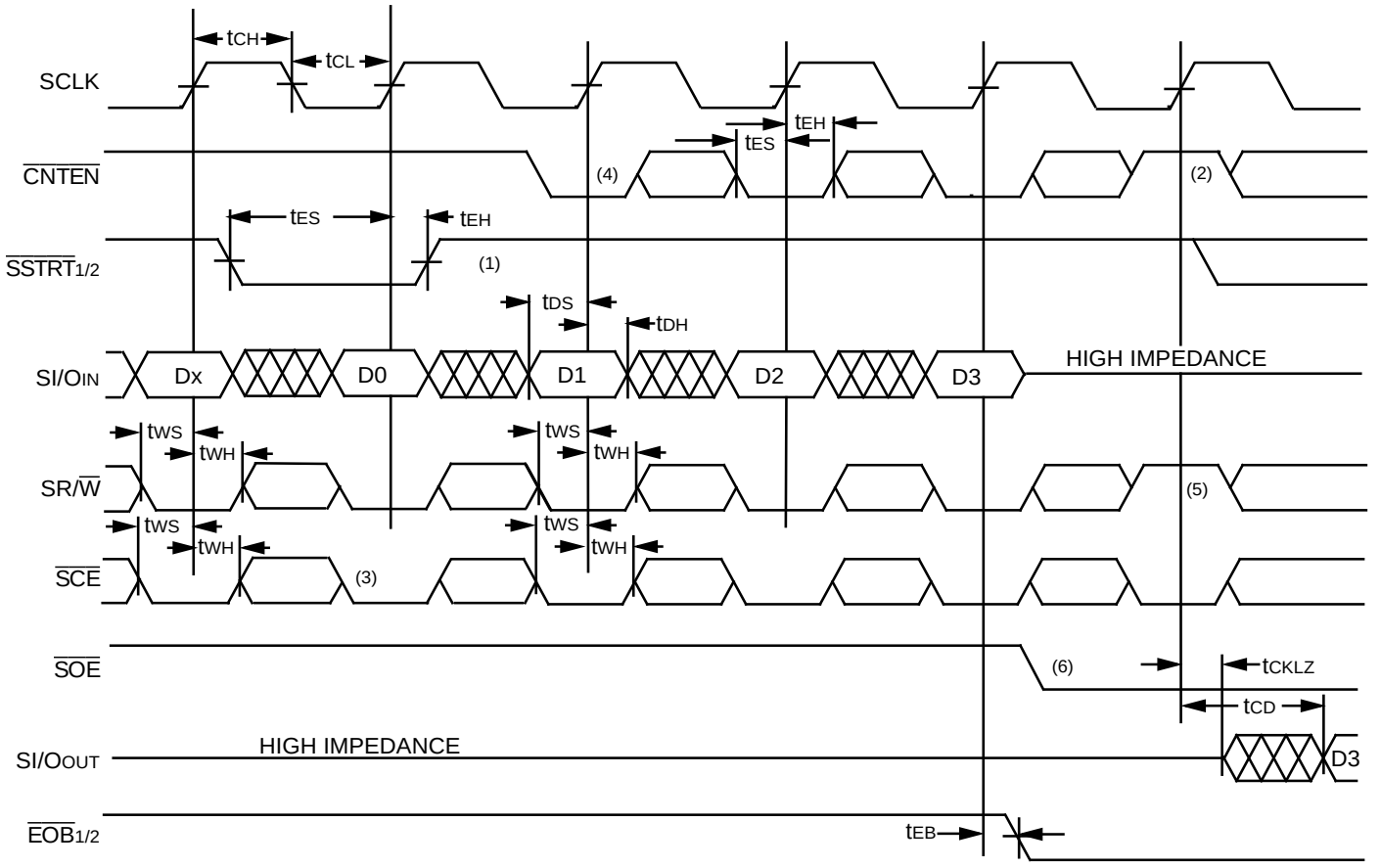


SEQUENTIAL PORT WAVEFORM: BURST WRITE CYCLES



NOTES :
1. If $\overline{SLD}$ = V_{IL}, then address will be clocked in on the SCLK's rising edge.
2. If $\overline{CNTEN}$ = V_{IH} for the SCLK's rising edge, the internal address counter will not advance.
3. Pointer is not incrementing on cycle immediately following $\overline{SLD}$ even if $\overline{CNTEN}$ is Low.
4. If SR/$\overline{W}$ = V_{IL}, data would be written to D0 again since $\overline{CNTEN}$ = V_{IH}.
5. $\overline{SOE}$ = V_{IL} makes no difference at this point since the SR/$\overline{W}$ = V_{IL} disables the output until SR/$\overline{W}$ = V_{IH} is clocked in on the next rising clock edge.

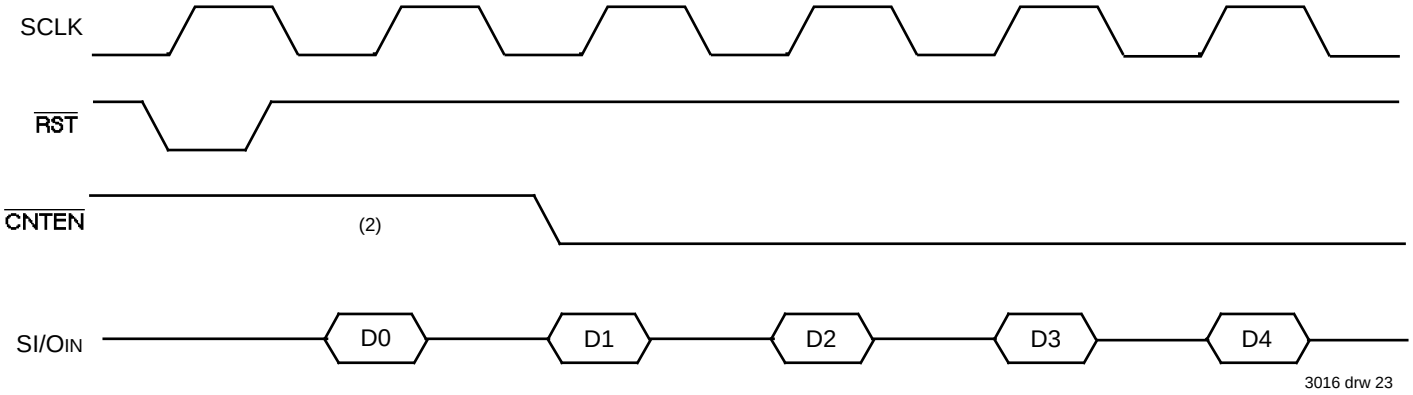
SEQUENTIAL PORT WAVEFORM: WRITE CYCLES (STRT/EOB FLAG TIMING)



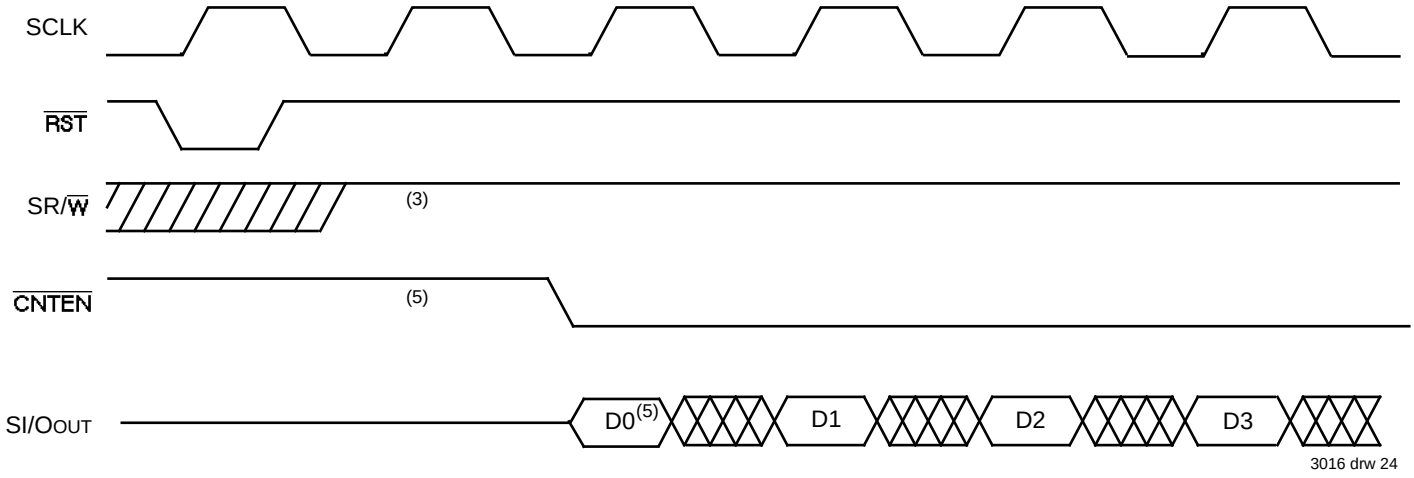
3016 drw 22

NOTES:
1. If $\overline{SSTRT_1}$ or $\overline{SSTRT_2}$ = V_{IL}, then address will be clocked in on the SCLK's rising edge.
2. If $\overline{CNTEN}$ = V_{IH} for the SCLK's rising edge, the internal address counter will not advance.
3. $\overline{SOE}$ will control the output and should be High on Power-Up. If $\overline{SCE}$ = V_{IL} and is clocked in while SR/$\overline{W}$ = V_{IH}, the data addressed will be read out within that cycle. If $\overline{SCE}$ = V_{IL} and is clocked in while SR/$\overline{W}$ = V_{IL}, the data addressed will be written to if the last cycle was a Read. $\overline{SOE}$ may be used to control the bus contention and permit a Write on this cycle.
4. Unlike $\overline{SLD}$ case, $\overline{CNTEN}$ is not disabled on cycle immediately following $\overline{SSTRT}$.
5. If SR/$\overline{W}$ = V_{IL}, data would be written to D0 again since $\overline{CNTEN}$ = V_{IH}.
6. $\overline{SOE}$ = V_{IL} makes no difference at this point since the SR/$\overline{W}$ = V_{IL} disables the output until SR/$\overline{W}$ = V_{IH} is clocked in on the next rising clock edge.

SEQUENTIAL COUNTER ENABLE CYCLE AFTER RESET, WRITE CYCLE(2, 4, 6)

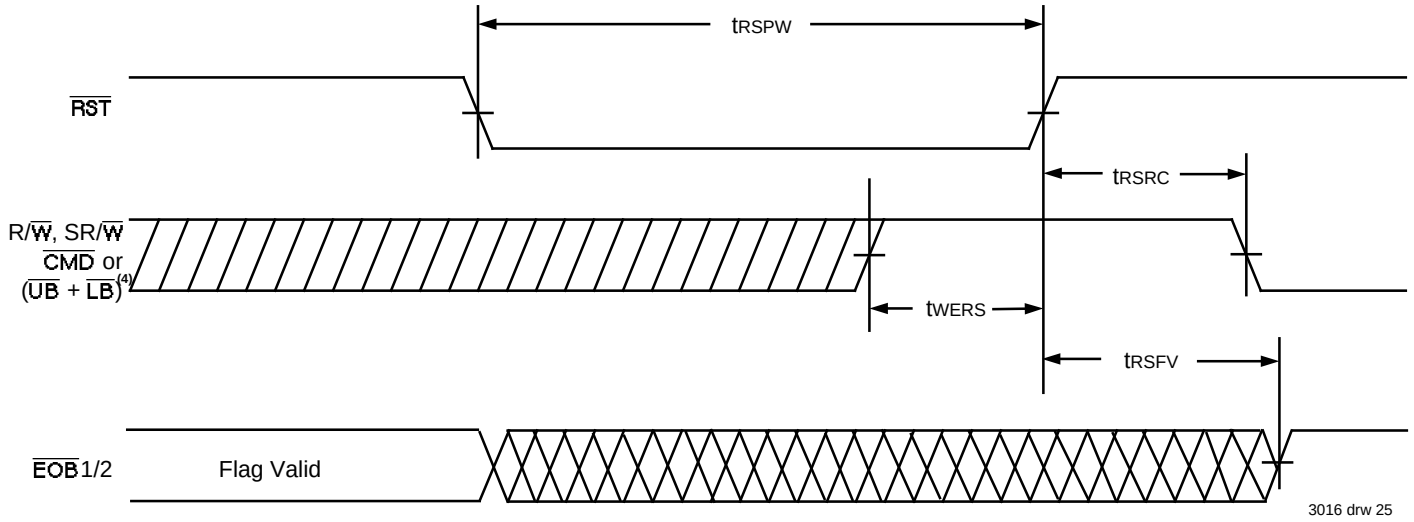


SEQUENTIAL COUNTER ENABLE CYCLE AFTER RESET, READ CYCLE(2, 4)

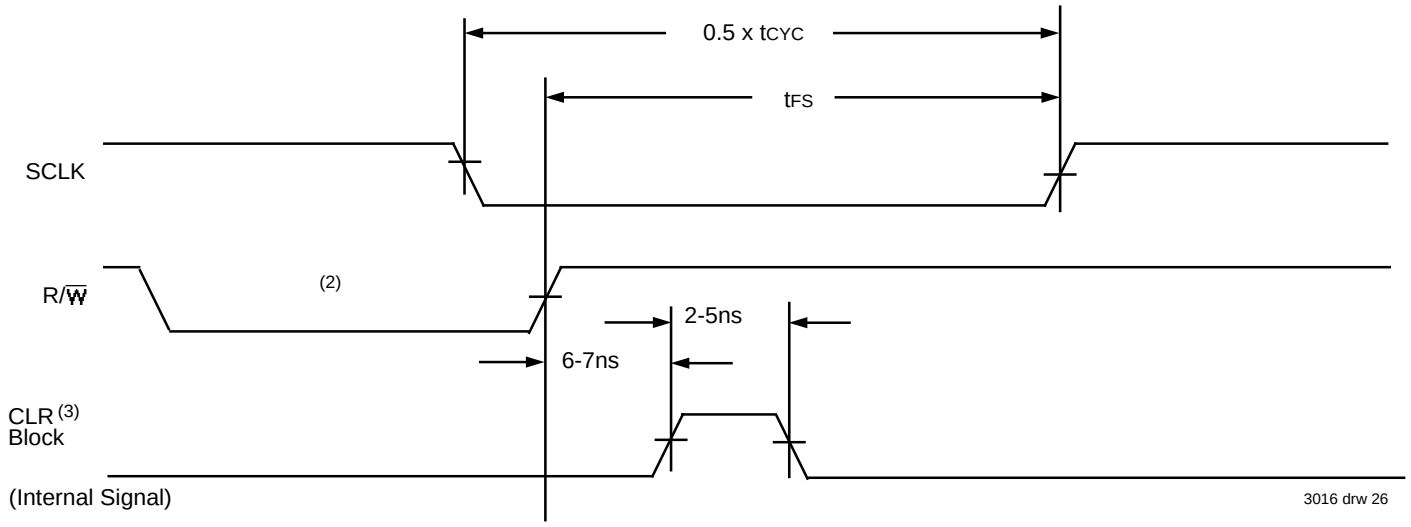


NOTES:
1. 'D0' represents data input for Address=0, 'D1' represents data input for Address=1, etc.
1. If $\overline{CNTEN}$=V_{IL} then 'D1' would be written into 'A1' at this point.
3. Data output is available at a t_{CD} after the SR/$\overline{W}$=V_{IH} is clocked. The $\overline{RST}$ sets SR/$\overline{W}$=Low internally and therefore disables the output until the next clock.
4. $\overline{SCE}$=V_{IL} throughout all cycles.
5. If $\overline{CNTEN}$=V_{IL} then 'D1' would be clocked out (read) at this point.
6. SR/$\overline{W}$=V_{IL}.

RANDOM ACCESS PORT WAVEFORM: RESET TIMING

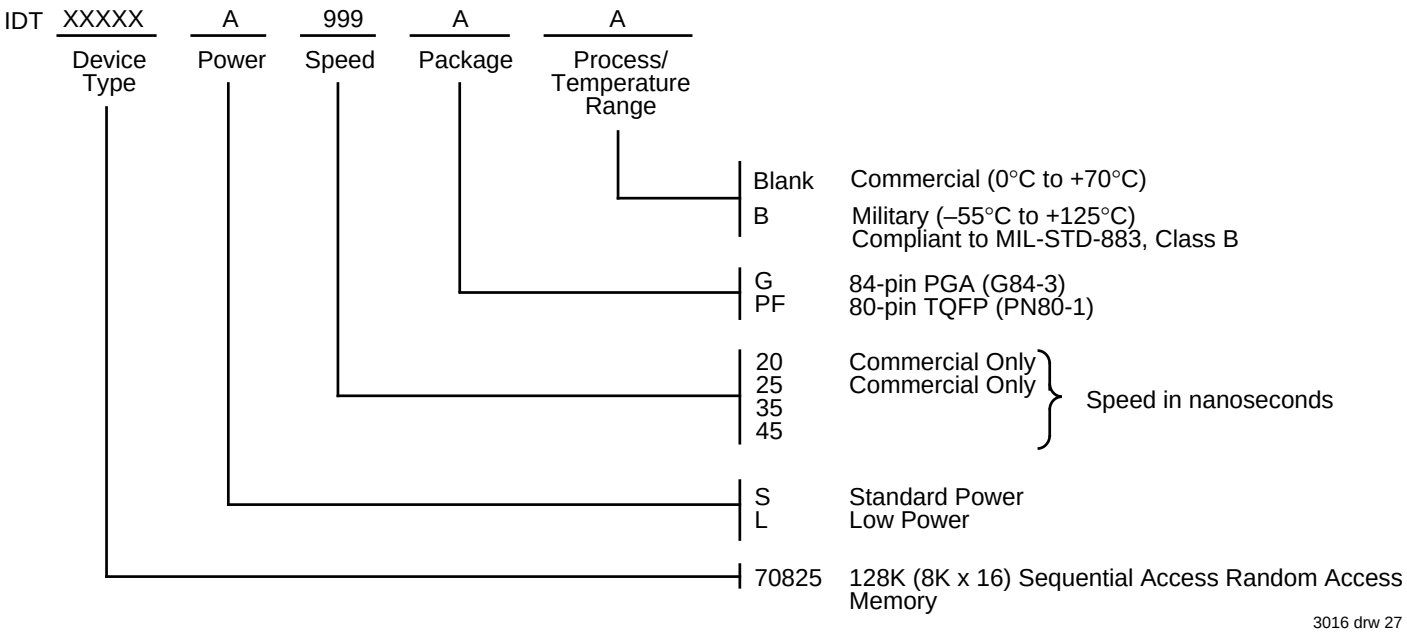


RANDOM ACCESS PORT WAVEFORM: RESTART TIMING OF SEQUENTIAL PORT (1)



NOTES:
1. The sequential port is in the STOP mode and is being restarted from the random port by the Bit 4 Counter Release (see Case 5).
2. "0" is written to Bit 4 from the random port at address [A2 - A0] = 100, when $\overline{CMD}$ = VIL and $\overline{CE}$ = VIH. The device is in the Buffer Command Mode (see Case 5).
3. CLR is an internal signal only and is shown for reference only.
4. Sequential port must also prohibit SR/$\overline{W}$ or $\overline{SCE}$ from being low for tWERS and tRSRC periods, or SCLK must not toggle from Low-to-High until after tRSRC.

ORDERING INFORMATION



3016 drw 27

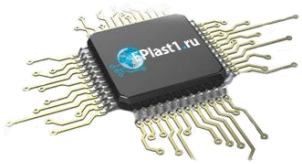
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.